

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	"6,486,037".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 15:41
L2	2	"6,566,734".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 16:31
L3	0	2003/0186511	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 16:31
L4	0	"210" and I3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 16:32
L5	773780	"210" or I3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 16:32
L6	5793	hdp	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 16:32
L7	1160	5 and 6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 16:32
L8	2	"5494697".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 16:32
L9	2	"5767018".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 16:32
L10	2	"6156629".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 16:32

L11	6	L8 or L9 or L10	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 16:32
L12	6	L11 or I3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 16:33
L13	1	12 and 6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 16:34
L14	2	"6027975".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 16:48
L15	2	"6027975".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 16:48
L19	1583293	"32" and "33"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 16:55
L20	142419	implant	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 16:55
L21	7830880	in	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 16:55
L22	1562306	channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 16:55
L23	0	L20 adj L21 adj L22	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 16:55

L24	0	L22 and L23	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 16:56
L25	41	"5252881"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 16:57
L26	2	"5252881".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 16:57
L27	2	"6077755".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 16:58
L28	618	pad adj oxide same RIE	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 16:58
L29	136207	HF	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 16:58
L30	26536	NH3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 16:59
L31	3	28 and 30	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 16:59
L32	3	31 and 29	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 16:59
L33	6	etch near oxide same (NH3 or NHx or NHHH or NHsubx or NHsubNH or "NH.subx" or "NH.subNH" or "NH.sub.x" or "NH.sub.NH")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 17:06

L34	5	33 and (HF or hydrofluric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 17:05
L35	5432	RIE and (HF or hydrofluric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 17:06
L36	67	35 and (NH3 or NHx or NHNH or NHsubx or NHsubNH or "NH.subx" or "NH.subNH" or "NH.sub.x" or "NH.sub. NH")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 17:10
L37	1	34 and (pad adj oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 17:07
L38	58	HF near (NH3 or NHx or NHNH or NHsubx or NHsubNH or "NH.subx" or "NH.subNH" or "NH.sub.x" or "NH.sub. NH")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 17:10
L39	3	38 and (pad adj oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 18:14
L40	0	High near plasma near oxide adj mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 18:15
L41	2	High near plasma same oxide adj mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 18:15
L42	7	HDP same oxide adj mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 18:16
L43	0	42 and nitrid near cvd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 18:17

L44	0	42 and nitride near cvd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 18:17
L45	0	39 and ash	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 18:18
L46	0	42 and ash	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 18:18
L47	0	silicon adj Nitride near thickness near nm	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 18:19
L48	223	silicon adj Nitride near thickness near nm	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 18:19
L49	44	48 and MOSFET	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 18:19
L50	13	49 and stop	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 18:20
L51	0	50 and CAdkissonD	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 18:22
L52	13	50 and Cvd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 18:43
L53	7	hdp same oxide adj mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 18:53

L54	1269	polysilicon and plasma same HBr	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 18:54
L55	315	polysilicon and plasma near etch same HBr	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 18:54
L56	20	55 and KOH	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 18:54
L57	148	polysilicon same plasma near etch same HBr	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 18:54
L58	11	57 and KOH	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 19:04
L59	2	"5360995".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 19:15
L60	2	"5620922".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 19:22
L61	306	remove hard adj mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 19:23
L62	335	implant near polysilicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 19:25
L63	0	61 and 62	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 19:23

L64	227	polysilicon near gate near mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 19:25
L65	142419	implant	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 19:25
L66	2	65 near 64	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 19:32
L67	0	source near extensions near nm	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 19:32
L68	10	(source or s/d) same extensions near nm	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 19:32
S2	2	"6064092".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:54
S3	1	"20050170570"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:38
S4	1911895	oxide or oxygen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 08:41
S5	142419	implant	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 08:37
S6	1292034	concentration	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 08:37

S7	89878	dopant	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 08:38
S8	1719	S4 near S7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 08:38
S9	1457	S4 near S5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 08:38
S10	36	S8 and S9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 08:38
S11	29	S10 and S6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 08:38
S12	798306	oxygen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 08:41
S13	395	S12 near S7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 08:41
S14	929	S12 NEAR S5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 08:41
S15	18	S13 AND S14	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 08:50
S16	486	S5 ADJ S12	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 08:51



S19	18347	locos	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 08:52
S20	41	S16 and S19	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 08:52
S21	1	10/725848	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 16:11
S22	185175	ultra	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:05
S23	1490498	thin	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:05
S24	1562306	channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:05
S25	46	S22 adj S23 adj S24	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:05
S26	28005	SOI	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:06
S27	55525	S25 ans S26	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:06
S28	38	S25 and S26	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:17
S29	11	("6420218").URPN.	USPAT	OR	ON	2005/09/15 09:10

S30	142419	implant	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:17
S31	7830880	in	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:17
S32	1562306	channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:18
S34	1294	S32 adj S30	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:19
S36	508	oxygen adj implant	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:19
S40	3489	SIMOX	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:38
S41	84289	mosfet	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:21
S42	1290	S40 and S41	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:22
S43	1332	thin adj channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:31
S44	28005	SOI	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:22

S45	78463	low adj resistance	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:22
S46	5811	low adj capacitance	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:22
S47	31	S42 and S43	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:23
S48	31	S47 and S44	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:23
S49	5	S48 and S45	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:30
S50	2	S49 and S46	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:23
S52	46	ultra adj thin adj channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:32
S53	20	S52 and S40	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:37
S54	1684	SIMO	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:38
S55	157	SIMOX.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:39

S56	0	S55 and (channel near implant)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:39
S57	18	S55 and channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:40
S58	67146	anneal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:40
S59	47	S55 and S58	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 10:06
S60	1040	thin\$3 near SOI	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:41
S61	223	ultra adj thin\$3 near SOI	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:41
S62	4	S59 and S60	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:41
S63	0	S59 and S61	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:41
S64	2	"6420218".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:54

S65	40	("4683645"   "4745082"   "4784718"   "5017504"   "5264382"   "5270232"   "5349228"   "5374575"   "5391510"   "5393685"   "5429956"   "5434093"   "5478776"   "5538913"   "5576227"   "5593907"   "5607884"   "5668397"   "5675159"   "5716861"   "5726081"   "5736435"   "5793090"   "5801075"   "5811323"   "5814544"   "5817558"   "5824586"   "5825066"   "5856225"   "5858843"   "5904530"   "5915180"   "5915182"   "5915183"   "5937297"   "5953602"   "5972754"   "5998288"   "6190952").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/09/15 09:59
S71	136935	silicon adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 10:07
S72	8652	pad adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 10:07
S73	28005	SOI	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 10:07
S74	10	burried near oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 10:07
S75	2038044	substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 10:07
S76	676	S71 and S72 and S73 and74 and S75	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 10:07
S77	3489	simox	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 10:07

S78	219	S76 and S77	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 11:11
S79	104	257/243	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 11:09
S80	1	S79 and simox	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 11:10
S81	1	SIMO.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 11:11
S82	157	SIMOX.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 12:09
S83	2	"6417078".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 12:49
S84	9757	soi adj substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 12:50
S85	978	dielectric adj mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 12:49
S88	87	soi near mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 12:53
S89	283	soi near channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 12:54

S90	5261	soi same channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 12:53
S91	98	S89 and simox	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 13:01
S92	2	"6417078".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 13:15
S93	84289	MOSFET	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 13:15
S96	1290	S93 and SIMOx	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 13:16
S98	12383	hard adj mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 13:16
S99	491787	dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 13:16
S10 0	353	S98 near S99	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 13:16
S10 1	8	S96 and S100	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 13:21
S10 2	235	simox same mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 13:38

S10 3	0	simox adj mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 13:21
S10 4	1	09/955375	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 13:23
S10 5	0	"6551898.pn",	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 13:39
S10 6	2	"6551898".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 13:51
S10 7	2	"20040241916"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 13:51
S10 8	198	ibis.as.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 13:56
S10 9	25	S108 and simox	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 13:52
S11 0	769242	mitsubishi.as.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 13:56
S11 1	200	S110 and simox	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 13:57
S11 2	122	S111 and mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 14:03



S11 3	0	S111 and (dielectric near mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 14:03
S11 4	59	simox and (dielectric near mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 15:31
S11 5	8652	pad adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 17:03
S11 6	3489	simox	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 16:12
S11 7	136935	silicon adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 16:12
S11 8	225	S115 and S116 and S117	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 16:57
S11 9	3809	S115 same S117	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 16:57
S12 0	3	S119 same S116	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 17:02
S12 1	5049	S115 and S117	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 17:03
S12 3	545	channel adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 17:04

S12 5	3	S123 same S115	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 17:05
S12 6	486	implant adj oxygen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 17:12
S12 9	2	"20020102813"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 17:09
S13 0	30	S126 and S115	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 17:42
S13 1	77366	dummy	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 17:42
S13 2	964798	gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 17:42
S13 3	1880164	region	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 17:42
S13 4	180	S131 near S132 near S133	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 17:42
S13 5	16	S134 and simox	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:01
S13 6	2586656	gate region	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:01

S13 7	17963	gate adj region	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:02
S13 8	8652	pad adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:02
S13 9	5793	HDP	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:02
S14 0	114444	polysilicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:02
S14 1	413620	resist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:19
S14 2	199	oxygen adj ash	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:23
S14 3	156502	photoresist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:19
S14 4	15560	thermal adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:19
S14 5	114444	polysilicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:19
S14 6	44	(poly near etch) same HBr	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:22

S14 8	1411	(Silicon adj Nitride) near cvd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:20
S14 9	1550701	selective or selectivity or selectively	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:21
S15 0	13626	(pad adj oxide) nead HDP	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:21
S15 1	0	.hF near NH3 near pad	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:21
S15 2	17	(hF near NH3) and oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:22
S15 7	120	S148 and S149 and S150	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:24
S15 8	143	S142 and S143 and S143	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:24
S15 9	7538	S144 and S145	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:25
S16 0	0	S157 and S158 and S159	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:25
S16 1	10	S158 and S159	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:25

S16 2	2	S161 and S150	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:26
S16 3	0	S161 and S148	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:26
S16 4	435	forming adj dummy adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:27
S16 5	251	dummy adj gate.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:29
S16 6	88	S165 and source and drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 07:35
S16 7	1550	form near gate near structure	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 07:36
S16 8	84289	MOSFET	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 07:36
S16 9	532	S167 and S168	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 07:37
S17 0	142163	cvd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 07:37
S17 1	5793	hdp	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 07:37

S17 2	9	S169 and S170 and S171	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 07:38
S17 3	61549	International adj Business adj machines	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:12
S17 4	80176	"169" and "173"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:12
S17 5	1007	S174 and cvd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:12
S17 6	22	S175 and hdp	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:13
S17 7	22	S176 and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:15
S17 8	2084	dummy adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:15
S17 9	30	"173" and S178	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:18
S18 0	0	S179 and (pad adj oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:19
S18 1	8652	pad adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:19

S18 2	163	S181 and S178	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:23
S18 3	0	S182 and "173"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:19
S18 4	2	09/809211	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:54
S18 5	519	silicon adj oxide adj mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:55
S18 6	1	S185 near hdp	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:56
S18 7	1	S185 same hdp	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:55
S18 8	127337	silicon adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:55
S18 9	120	S188 near hdp	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:59
S19 0	21	nitride near cvd near pecvd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:06
S19 1	21	S190 and nm	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:06

S19 3	141789	((silicon adj nitride) or (SiN4 or SiNn or "SiN.sub4" or "SiN.subx" or "SiN. subn" or "SiN.sub.4" or "SiN.sub.x" or "SiN.sub.n"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:06
S19 4	22	S193 near cvd near pecvd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:09
S19 5	1449	S193 near cvd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:07
S19 6	1762	S193 near (nm or angstroms)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:10
S19 7	3	S196 near mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:09
S19 8	1236	S193 near nm	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:10
S19 9	233	S198 same mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:17
S20 0	6801	etch\$3 near under	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:19
S20 1	65	etch\$3 near under near resist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:38
S20 2	9	etch near polysilicon near HBr	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:54



S20 3	0	remove near resist near oxygen near ash	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:42
S20 4	3	remove near resist near ash same (oxygen or O2 or Ox or On or Osubx or Osubn or "O.subx" or "O.subn" or "O.sub.x" or "O.sub.n")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:43
S20 5	567	remove near resist same (oxygen or O2 or Ox or On or Osubx or Osubn or "O.subx" or "O.subn" or "O.sub.x" or "O.sub.n")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:45
S20 6	2	"5494697".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:47
S20 7	2	"5767018".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:47
S20 8	2	"6156629".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:47
S20 9	0	S206 and S207 and S208	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:47
S21 0	6	S206 or S207 or S208	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 16:32
S21 1	2	S210 and selectivity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:47
S21 2	8	S202 and (selectivity or selective or selectively)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:55

S21 3	0	KOH near polysilicon near (selectivity or selective or selectively)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:55
S21 4	2	KOH near polysilicon near etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:56
S21 5	9	KOH near polysilicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:59
S21 6	2	"6566734"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 11:28
S21 7	395	polysilicon near (thermal adj oxidation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 11:10
S21 8	15	S217 near gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 11:11
S21 9	2025025	nitride selective to oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 11:14
S22 0	9	etch adj nitride near selective near oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 11:16
S22 1	43	etch adj nitride near selective	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 11:18
S22 2	1443483	oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 11:16

S22 3	9	S221 near S222	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 11:16
S22 4	0	pad adj oxide near etch near (NF and NH3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 11:19
S22 5	0	pad adj oxide near etch near (NF3 or NFx or NFNF or NFsubx or NFsubNF or "NF.subx" or "NF.subNF" or "NF.sub.x" or "NF.sub.NF")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 11:20
S22 6	0	pad adj oxide near (NF3 or NFx or NFNF or NFsubx or NFsubNF or "NF.subx" or "NF.subNF" or "NF.sub.x" or "NF.sub.NF")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 11:20
S22 7	0	etch adj oxide near (NF3 or NFx or NFNF or NFsubx or NFsubNF or "NF.subx" or "NF.subNF" or "NF.sub.x" or "NF.sub.NF")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 11:20
S22 8	1	etch near oxide near (NF3 or NFx or NFNF or NFsubx or NFsubNF or "NF.subx" or "NF.subNF" or "NF.sub.x" or "NF.sub.NF")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 11:20
S22 9	11	etch near oxide same (NF3 or NFx or NFNF or NFsubx or NFsubNF or "NF.subx" or "NF.subNF" or "NF.sub.x" or "NF.sub.NF")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 11:25
S23 2	1145	doped polysilicon gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 11:28
S23 3	2440	remove mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 19:22
S23 7	57	implant near source/drain near ((IIIA and v) or (n+ and p+))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 11:34

S23 9	1617	source/drain adj extension	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 11:47
S24 3	1948221	thickness	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 11:37
S24 4	11	S239 near S243	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 11:37
S24 9	1139	extension near thickness	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 11:41
S25 0	1	S249 near (s/d or source/drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 11:42
S25 1	1688	(source/drain or s/d) adj extension	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 11:48
S25 2	11	S251 near S243	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 11:48
S25 3	337	S251 same S243	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 13:10
S25 4	57	Si near SiGe near SiGeC near SiC	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 13:11
S25 5	4	etch near oxide same ((NH3 or NHx or NHNH or NHsubx or NHsubNH or "NH.subx" or "NH.subNH" or "NH.sub.x" or "NH.sub.NH") and HF)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 13:45